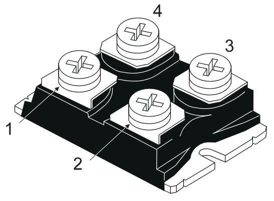
ESM2012DV

NPN DARLINGTON POWER MODULE

- HIGH CURRENT POWER BIPOLAR MODULE
- VERY LOW R_{th} JUNCTION TO CASE
- SPECIFIED ACCIDENTAL OVERLOAD AREAS
- ULTRAFAST FREEWHEELING DIODE
- FULLY INSULATED PACKAGE (UL COMPLIANT)
- EASY TO MOUNT
- LOW INTERNAL PARASITIC INDUCTANCE

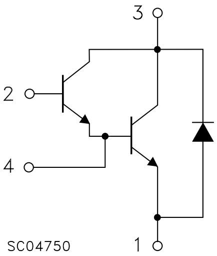
INDUSTRIAL APPLICATIONS:

- MOTOR CONTROL
- UPS
- DC/DC & DC/AC CONVERTERS



ISOTOP

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage (V_{BE} = -5 V)	150	V
$V_{CEO(sus)}$	Collector-Emitter Voltage (I_B = 0)	120	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	7	V
I_C	Collector Current	120	A
I_{CM}	Collector Peak Current (t_p = 10 ms)	180	A
I_B	Base Current	2	A
I_{BM}	Base Peak Current (t_p = 10 ms)	4	A
P_{tot}	Total Dissipation at T_c = 25 ^oC	175	W
V_{isol}	Insulation Withstand Voltage (RMS) from All Four Terminals to Exernal Heatsink	2500	V
T_{stg}	Storage Temperature	-55 to 150	^oC
T_j	Max. Operating Junction Temperature	150	^oC

THERMAL DATA

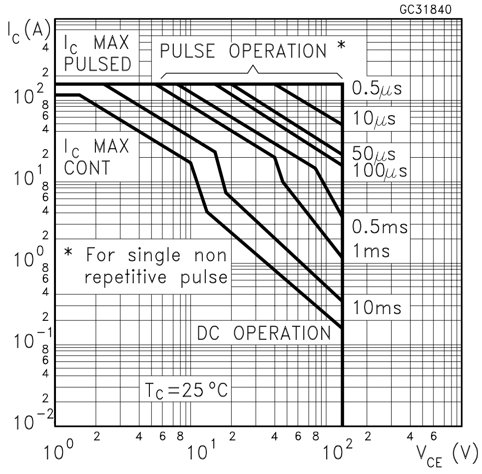
$R_{thj-case}$	Thermal Resistance Junction-case (transistor)	Max	0.7	°C/W
$R_{thj-case}$	Thermal Resistance Junction-case (diode)	Max	0.9	°C/W
R_{thc-h}	Thermal Resistance Case-heatsink With Conductive Grease Applied	Max	0.05	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

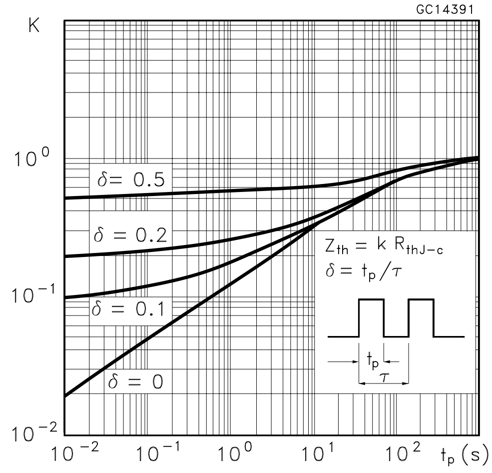
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CER} #	Collector Cut-off Current (R_{BE} = 5 Ω)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ T_j = 100 °C			1.5 10	mA mA
I_{CEV} #	Collector Cut-off Current (V_{BE} = -5V)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ T_j = 100 °C			1 7	mA mA
I_{EBO} #	Emitter Cut-off Current (I_C = 0)	V_{EB} = 5 V			1	mA
$V_{CEO(SUS)}$*	Collector-Emitter Sustaining Voltage (I_B = 0)	I_C = 5 A L = 15 mH V_{clamp} = 125 V	125			V
h_{FE}*	DC Current Gain	I_C = 100 A V_{CE} = 5 V		1200		
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 70 A I_B = 0.25 A I_C = 70 A I_B = 0.25 A T_j = 100 °C I_C = 100 A I_B = 1 A I_C = 100 A I_B = 1 A T_j = 100 °C		1.25 1.35 1.5 1.65	 1.5 2	V V V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 100 A I_B = 1 A I_C = 100 A I_B = 1 A T_j = 100 °C		2.3 2.35	 3	V V
di_C/dt	Rate of Rise of On-state Collector	V_{CC} = 90 V R_C = 0 t_p = 3 µs I_{B1} = 0.5 A T_j = 100 °C	200	230		A/µs
V_{CE}(3 µs)••	Collector-Emitter Dynamic Voltage	V_{CC} = 90 V R_C = 1.3 Ω I_{B1} = 0.5 A T_j = 100 °C		2	3	V
V_{CE}(5 µs)••	Collector-Emitter Dynamic Voltage	V_{CC} = 90 V R_C = 1.3 Ω I_{B1} = 0.5 A T_j = 100 °C		1.8	2.5	V
t_s t_f t_c	Storage Time Fall Time Cross-over Time	I_C = 70 A V_{CC} = 90 V V_{BB} = -5 V R_{BB} = Ω V_{clamp} = 125 V I_{B1} = 0.25 A L = 60 µH T_j = 100 °C		0.9 0.15 0.3	2 0.3 0.6	µs µs µs
V_{CEW}	Maximum Collector Emitter Voltage Without Snubber	I_{CWoff} = 120 A I_{B1} = 1A V_{BB} = -5 V V_{CC} = 90 V L = 60 µH R_{BB} = 1.25 Ω T_j = 125 °C	125			V
V_F*	Diode Forward Voltage	I_F = 100 A T_j = 100 °C		0.92	1	V
I_{RM}	Reverse Recovery Current	V_{CC} = 125 V I_F = 100 A di_F/dt = -200 A/µs L < 0.05 µH T_j = 100 °C		10	14	A

∗ Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
See test circuits in databook introduction
To evaluate the conduction losses of the diode use the following equations:
$V_F = 0.66 + 0.0034\ I_F$ $P = 0.66\ I_{F(AV)} + 0.0034\ I^2_{F(RMS)}$

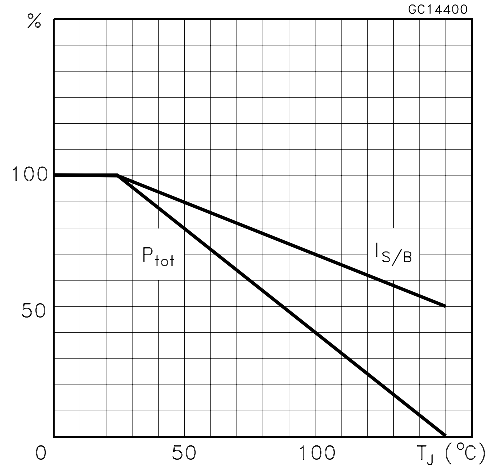
Safe Operating Areas



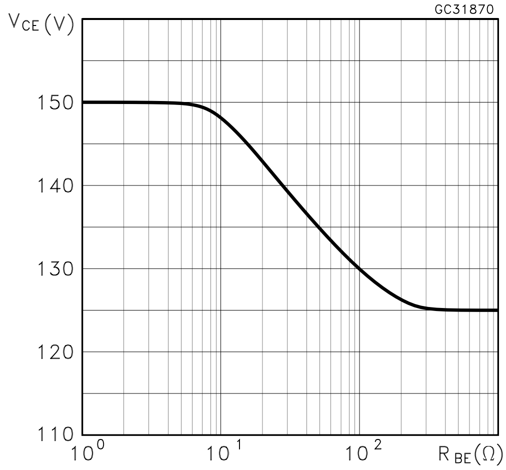
Thermal Impedance



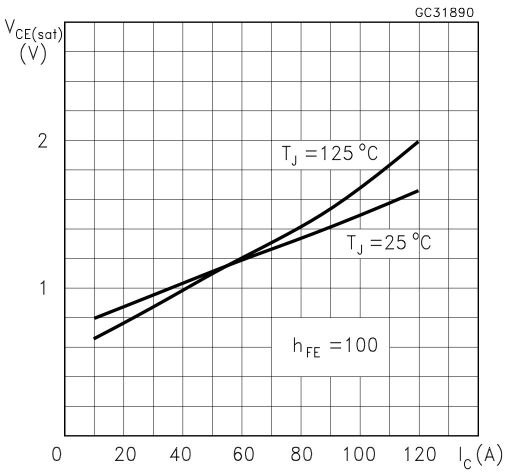
Derating Curve



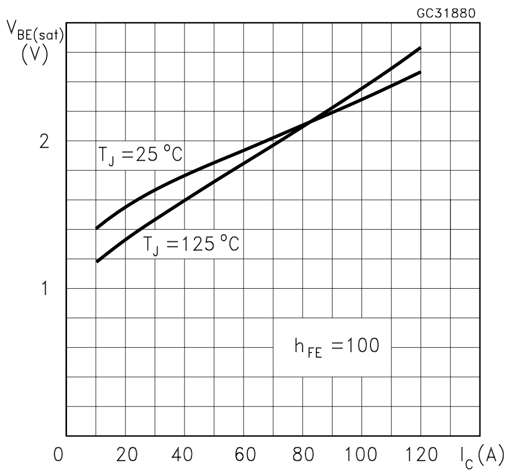
Collector-emitter Voltage Versus base-emitter Resistance



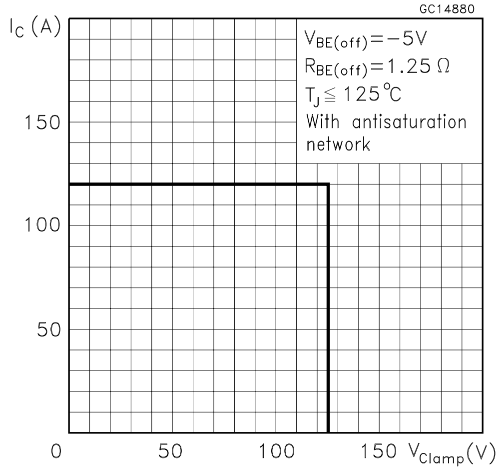
Collector Emitter Saturation Voltage



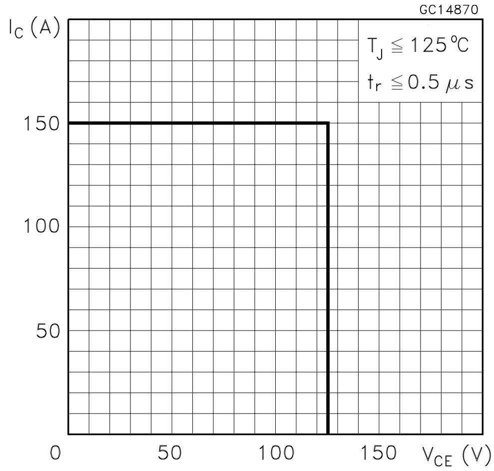
Base-Emitter Saturation Voltage



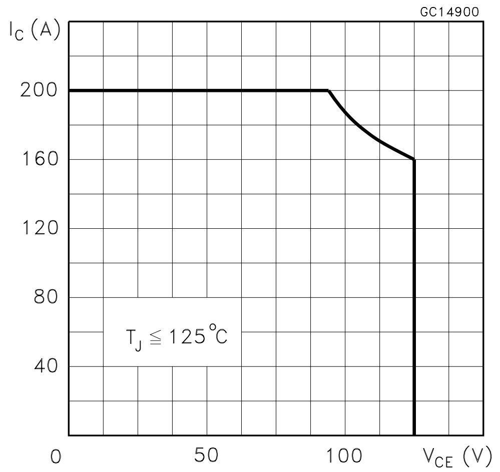
Reverse Biased SOA



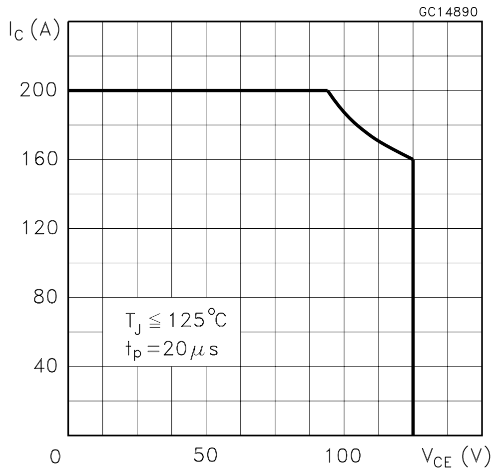
Foward Biased SOA



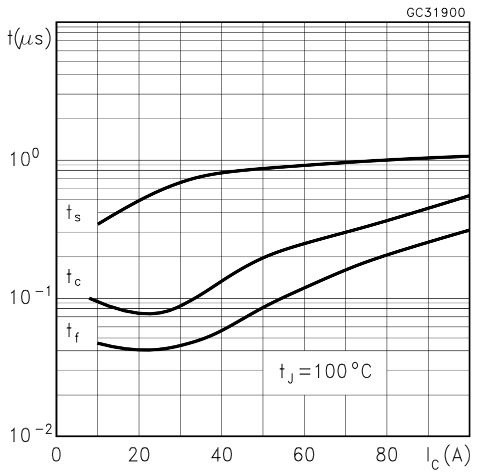
Reverse Biased AOA



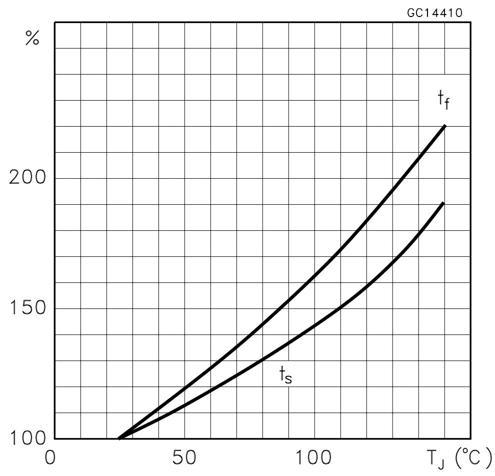
Forward Biased AOA



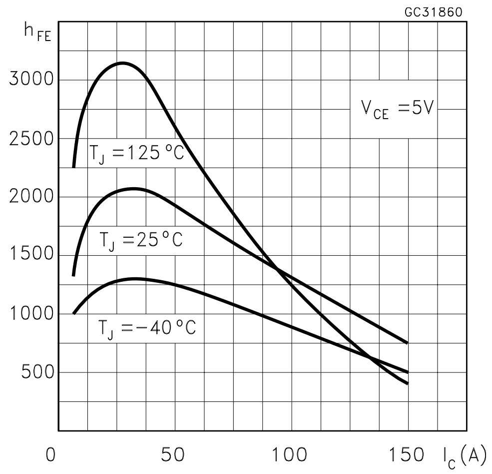
Switching Times Inductive Load



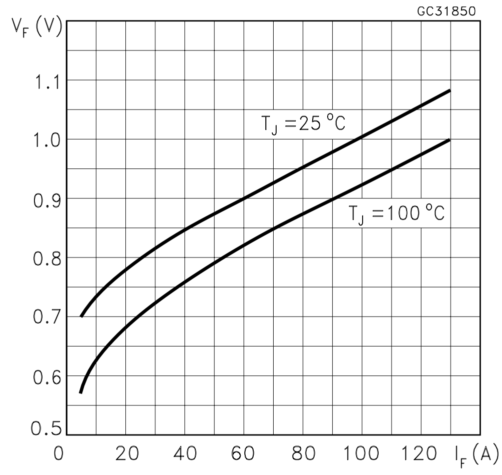
Switching Times Inductive Load Versus Temperature



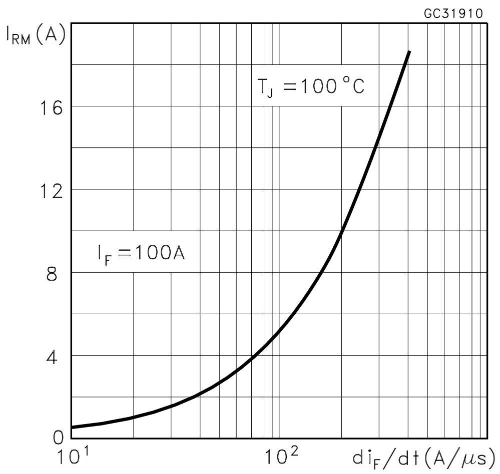
Dc Current Gain



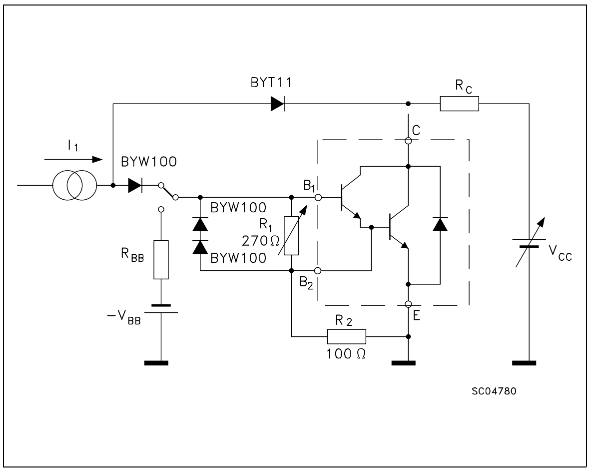
Typical V_F Versus I_F



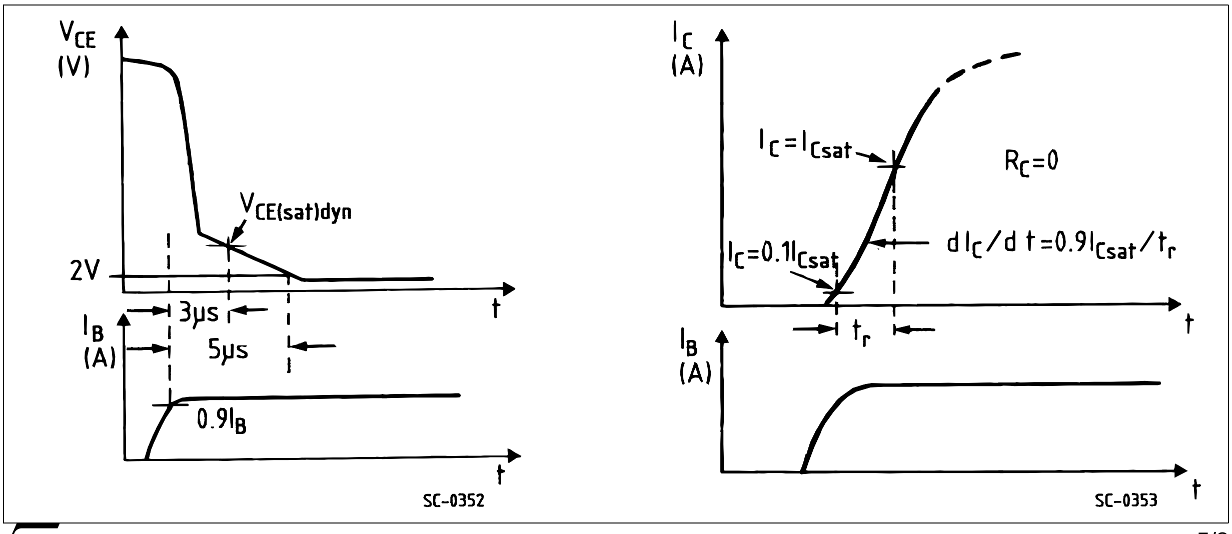
Peak Reverse Current Versus di_F/dt



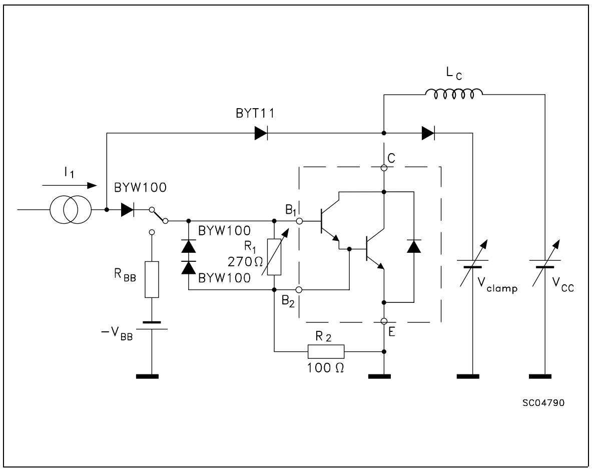
Turn-on Switching Test Circuit



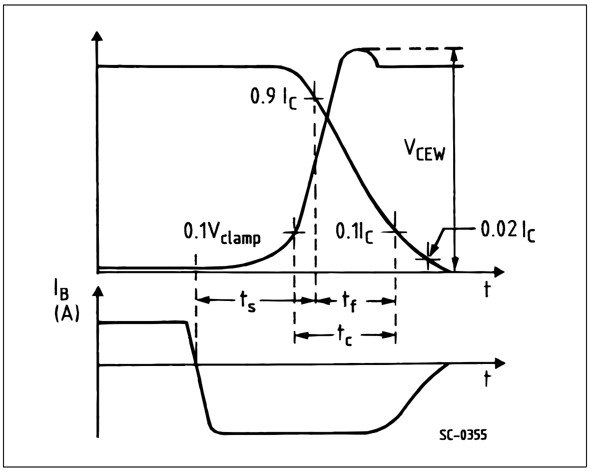
Turn-on Switching Waveforms



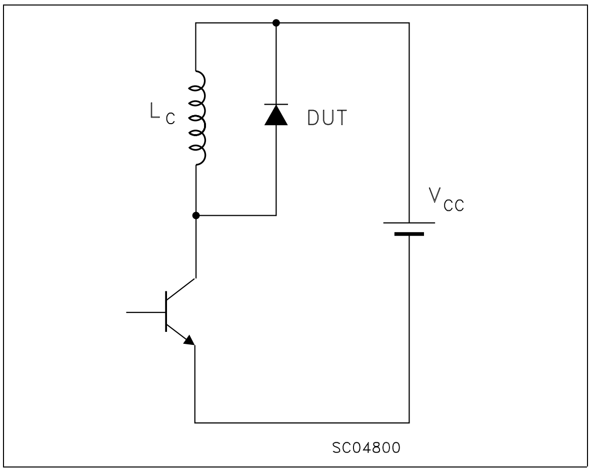
Turn-on Switching Test Circuit



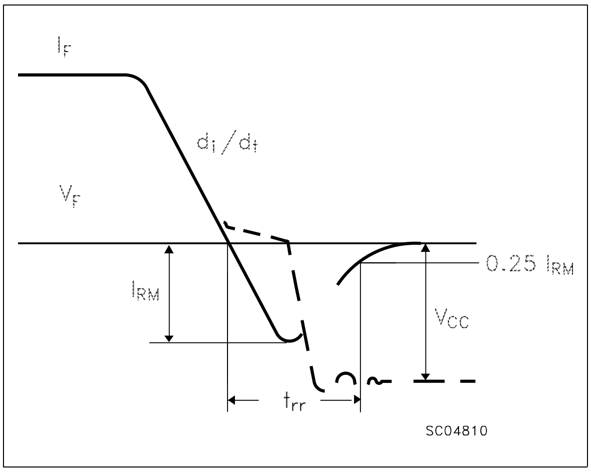
Turn-off Switching Waveforms



Turn-off Switching Test Circuit of Diode

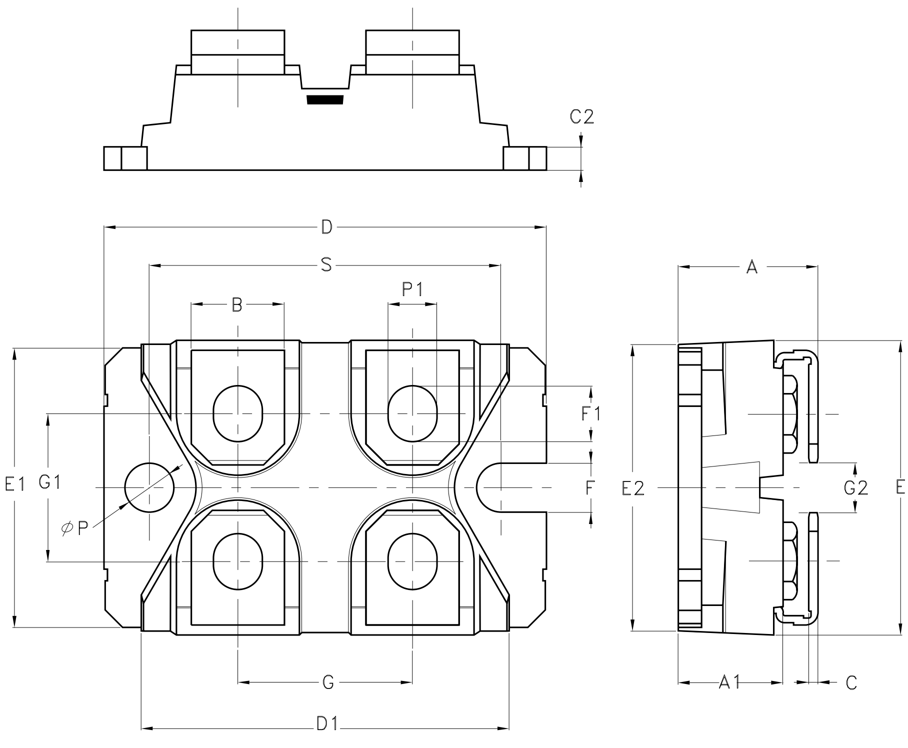


Turn-off Switching Waveform of Diode



ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.465		0.480
A1	8.9		9.1	0.350		0.358
B	7.8		8.2	0.307		0.322
C	0.75		0.85	0.029		0.033
C2	1.95		2.05	0.076		0.080
D	37.8		38.2	1.488		1.503
D1	31.5		31.7	1.240		1.248
E	25.15		25.5	0.990		1.003
E1	23.85		24.15	0.938		0.950
E2		24.8			0.976	
G	14.9		15.1	0.586		0.594
G1	12.6		12.8	0.496		0.503
G2	3.5		4.3	0.137		1.169
F	4.1		4.3	0.161		0.169
F1	4.6		5	0.181		0.196
P	4		4.3	0.157		0.169
P1	4		4.4	0.157		0.173
S	30.1		30.3	1.185		1.193



P093A